

Title (en)

METHOD FOR PRODUCING A SUBSTRATE, SUBSTRATE, METAL-OXIDE-SEMICONDUCTOR FIELD-EFFECT TRANSISTOR WITH A SUBSTRATE, MICRO-ELECTROMECHANICAL SYSTEM WITH A SUBSTRATE, AND MOTOR VEHICLE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES SUBSTRATS, SUBSTRAT, METALL-OXID-HALBLEITER-FELDEFFEKTTTRANSISTOR MIT EINEM SUBSTRAT, MIKROELEKTROMECHANISCHES SYSTEM MIT EINEM SUBSTRAT, UND KRAFTFAHRZEUG

Title (fr)

PROCÉDÉ PERMETTANT DE PRODUIRE UN SUBSTRAT, SUBSTRAT, TRANSISTOR À EFFET DE CHAMP MÉTAL-OXYDE-SEMI-CONDUCTEUR POURVU D'UN SUBSTRAT, SYSTÈME MICROÉLECTROMÉCANIQUE POURVU D'UN SUBSTRAT, ET VÉHICULE AUTOMOBILE

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Abstract (en)

[origin: WO2015032577A1] The present invention relates to a method for producing a substrate, a metal-oxide-semiconductor field-effect transistor with a substrate, a micro-electromechanical system with a substrate and a motor vehicle. The substrate concerned comprises a silicon carbide layer (10). The method for producing a substrate for a metal-oxide-semiconductor field-effect transistor or a micro-electromechanical system comprises the following steps: (a) dry etching of a preliminary trench into the substrate by using a structured first masking layer, wherein the dry etching is carried out in such a way that a remnant (60') of the first structured masking layer remains, (b) applying a second masking layer (65) at least to walls of the preliminary trench, and (c) dry etching by using the remnant (60') of the first masking layer and the second masking layer so as to produce a trench with a step in the trench.

IPC 8 full level

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